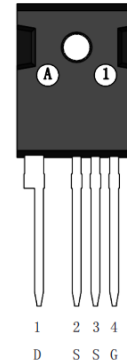


Description

Silicon Carbide (SiC) MOSFET use a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size.

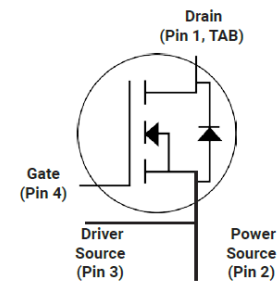
Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low RDS(on)
- Optimized package with separate driver source pin
- Easy to parallel and simple to drive
- ROHS Compliant, Halogen free



Application

- EV Charging
- High Voltage DC/DC Converters
- Switch Mode Power Supplies
- Power Factor Correction Modules



Ordering Information

Part Number	Marking	Package	Packaging
ASC30N1200MT4	ASC30N1200MT4	TO-247	Tube



ASC30N1200MT4

1200V N-Channel MOSFET

Absolute Maximum Ratings($T_c=25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	1200	V
I_D	Drain Current(continuous)at $T_c=25^{\circ}\text{C}$	32	A
I_D	Drain Current(continuous)at $T_c=100^{\circ}\text{C}$	23	A
I_{DM}	Drain Current (pulsed)	80	A
V_{GS}	Gate-Source Voltage	-10/+22	V
P_D	Power Dissipation $T_c = 25^{\circ}\text{C}$	145	W
T_J, T_{stg}	Junction and Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Typical Performance-Static

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	1200			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=1200\text{V}, V_{GS}=0\text{V}, T_J=25^{\circ}\text{C}$			100	μA
I_{GSS}	Gate-body Leakage Current	$V_{DS}=0\text{V}; V_{GS}=-10\text{ to }20\text{V}$			250	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=5\text{mA}$	2	3	4	V
$V_{GS(on)}$	Recommended turn-on Voltage	Static		20		V
$V_{GS(off)}$	Recommended turn-off Voltage			-5		V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS}=20\text{V}, I_D=20\text{A}$		80	100	$\text{m}\Omega$
		$V_{GS}=20\text{V}, I_D=20\text{A}$ $T_J=150^{\circ}\text{C}$		122		$\text{m}\Omega$

Typical Performance-Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input Capacitance	V _{DS} =1000V, f=1MHz, V _{AC} =25mV		1590		pF
C _{oss}	Output Capacitance			63		pF
C _{rss}	Reverse Transfer Capacitance			3.9		pF
g _{fs}	Transconductance	V _{DS} =20V, I _D =20A		12		S
E _{oss}	Coss Stored Energy	V _{DS} =1000V, f=1MHz		35.7		μ J
E _{ON}	Turn-On Energy (Body Diode)	V _{DS} =800V, V _{GS} =-5/20V, I _D =20A, L=150uH T _J =150°C		455		μ J
E _{OFF}	Turn-Off Energy (Body Diode)			111		μ J
Q _g	Total Gate Charge	V _{DS} =800V, V _{GS} =-5V/20V, I _D = 15 A		72		nC
Q _{gs}	Gate-source Charge			21		nC
Q _{gd}	Gate-Drain Charge			22		nC
R _{G (int)}	Internal Gate Resistance	f=1MHz, V _{AC} =25mV		3		Ω
t _{d(on)}	Turn-on Delay Time	V _{DS} =800V, V _{GS} =-5V/20V, I _D =20A, L=150 μ H Rext=2.5Ω		42		ns
t _r	Rise Time			15		ns
t _{d(off)}	Turn-off Delay Time			36		ns
t _f	Fall Time			11		ns

Typical Performance-Reverse Diode(T_J = 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{FSD}	Forward Voltage	V _{GS} =0V, I _F =10A, T _J =25°C		4.8	6	V
		V _{GS} =0V, I _F =10A, T _J =150°C		4.2	6	V
I _S	Continuous Diode Forward Current	V _{GS} =0V, T _C =25°C		27		A
t _{rr}	Reverse Recovery Time	V _{GS} =-5 V, I _F =20A, V _R =800 V, di/dt=900 A/μs, T _J =150°C		36		nS
Q _{rr}	Reverse Recovery Charge			297		nC
I _{rrm}	Peak Reverse Recovery Current			15.5		A

Thermal Characteristics

Symbol	Parameter	Value.	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	0.86	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	40	°C/W

The values are based on the junction-to case thermal impedance which is measured with the device mounted to a large heat sink assuming maximum junction temperature of T_J(max)=150°C

Electrical Characteristics

Fig1. Output characteristics ($T_J = 25^\circ\text{C}$)

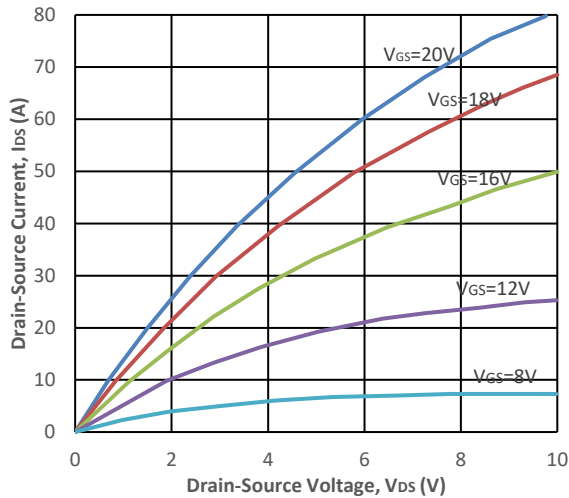


Fig2. Output characteristics ($T_J = 150^\circ\text{C}$)

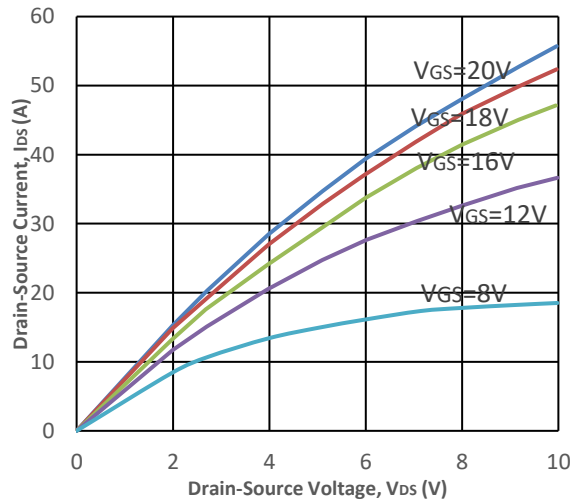


Fig3. Normalized On-Resistance vs. Temperature

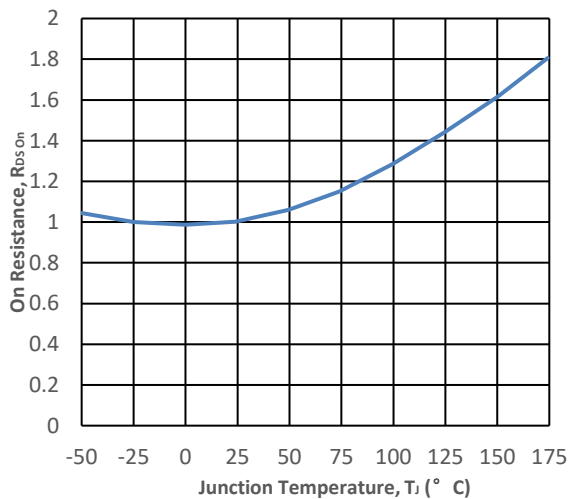


Fig4. On-Resistance vs. Temperature

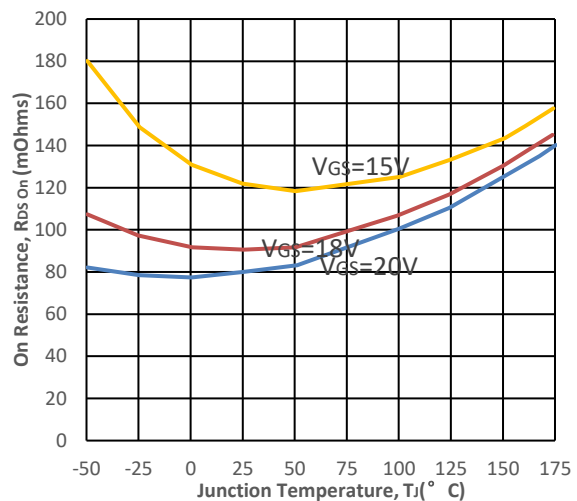


Fig5. Transfer Characteristic

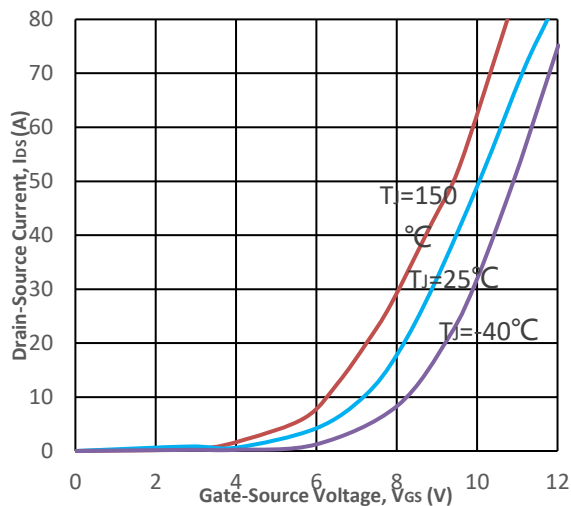


Fig6. Body Diode Characteristic at 25°C

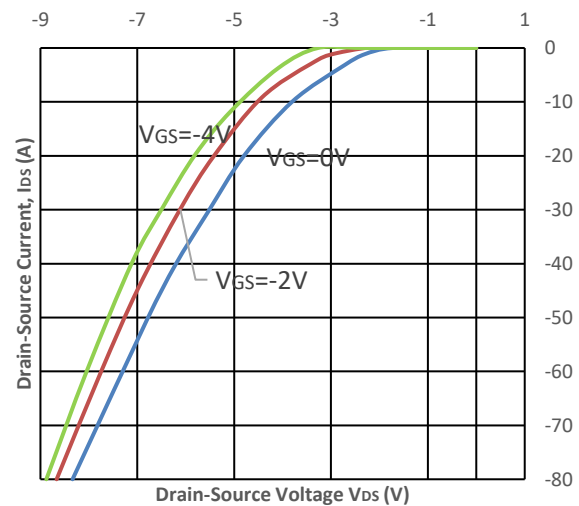


Fig7. Threshold Voltage vs. Temperature

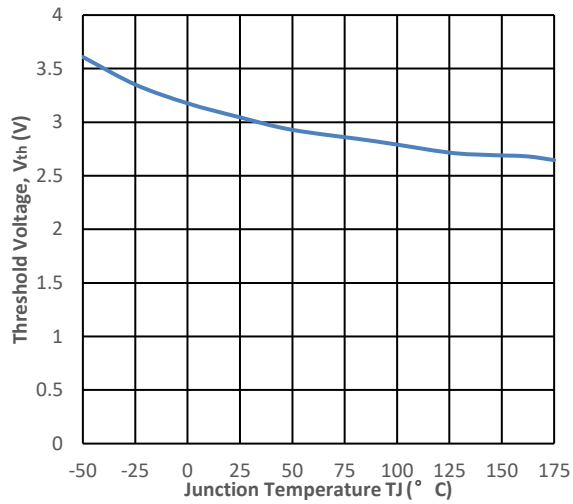


Fig8. Gate Charge Characteristics

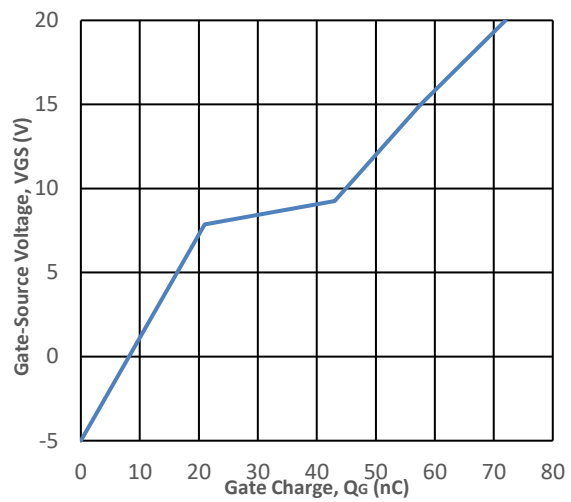


Fig9. 3rd Quadrant Characteristic at 25 $^{\circ}$ C

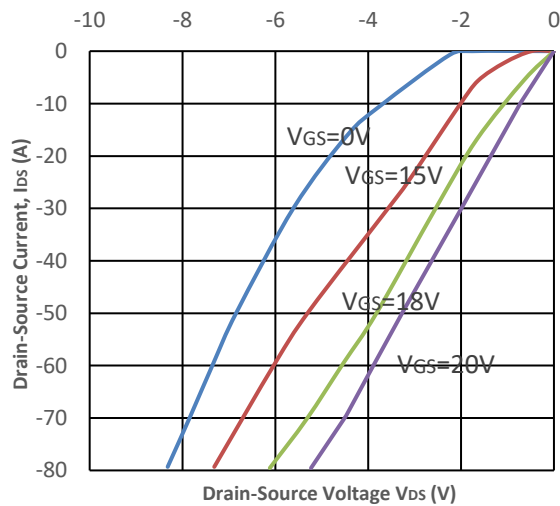


Fig10. Output Capacitor Stored Energy

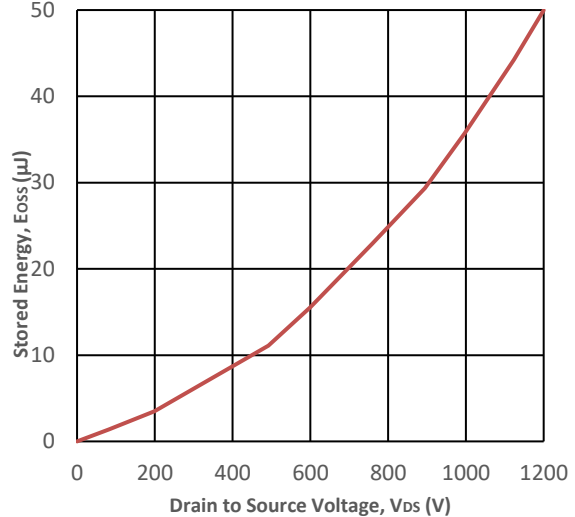


Fig11. Capacitances vs. Drain-Source

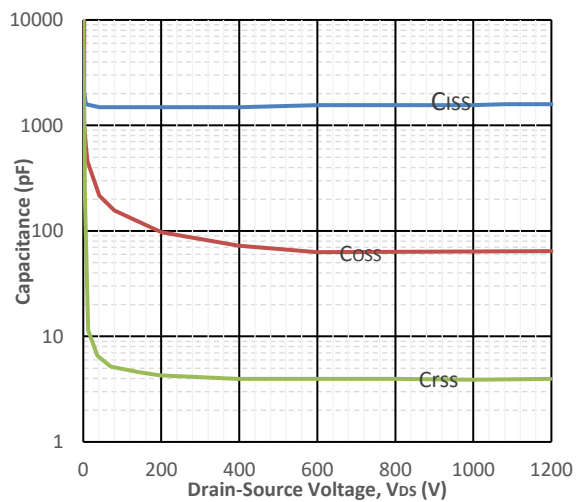


Fig12. Max Power Dissipation Derating Vs T_c

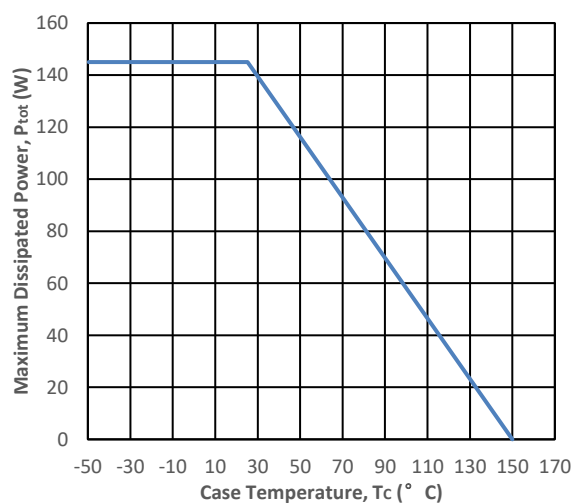


Fig13. Switching Energy vs. Drain Current

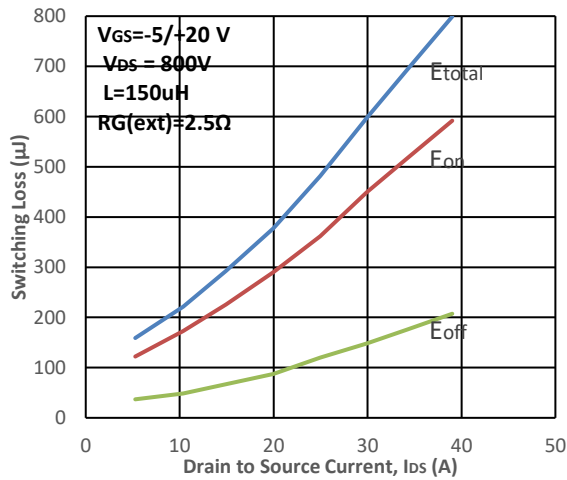


Fig14. Switching Energy vs. $R_{G(\text{ext})}$

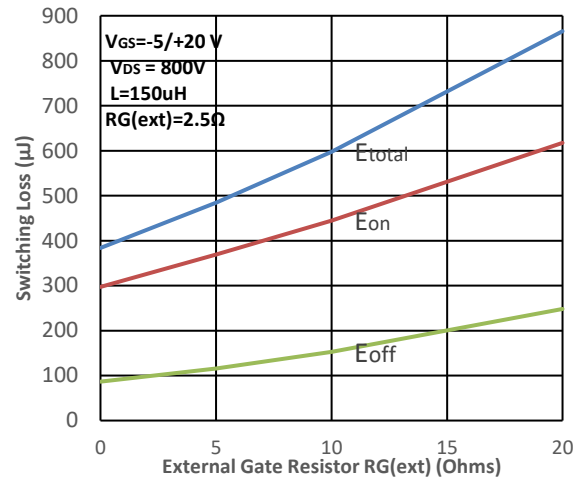


Fig15. Switching Energy vs. Temperature

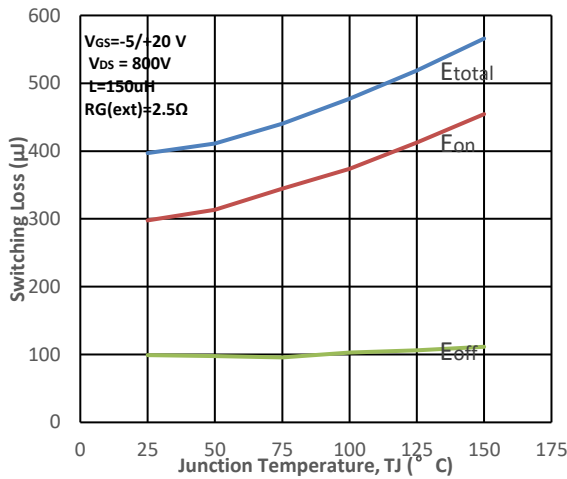


Fig16. Switching Times vs. $R_{G(\text{ext})}$

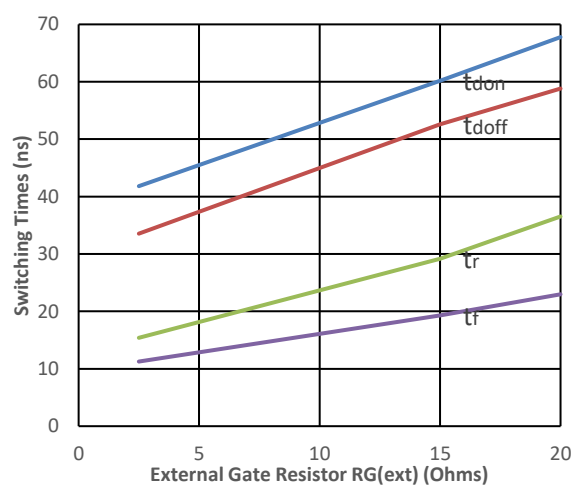


Fig17. Transient Thermal Impedance

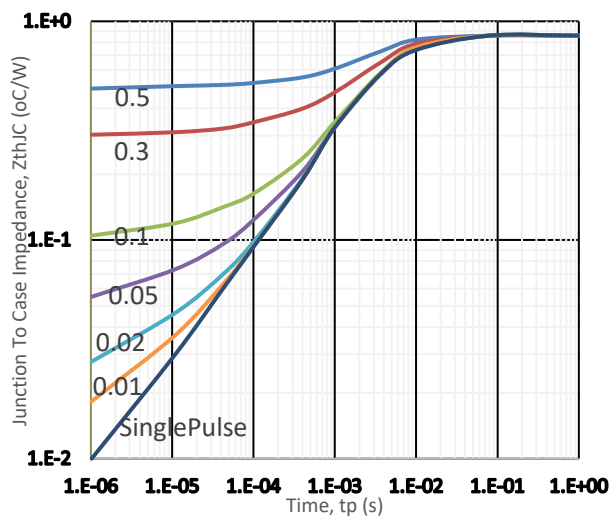
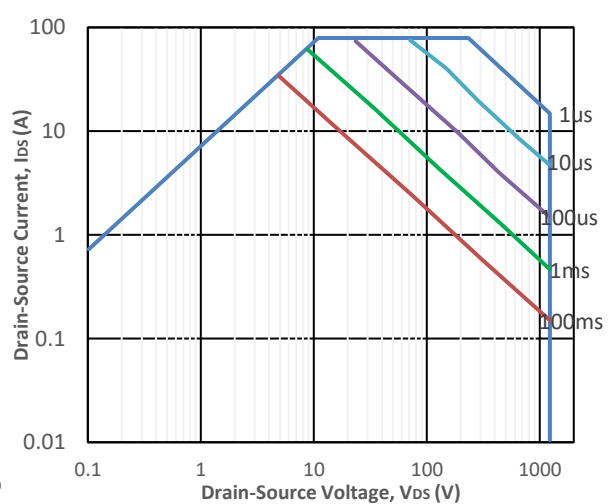
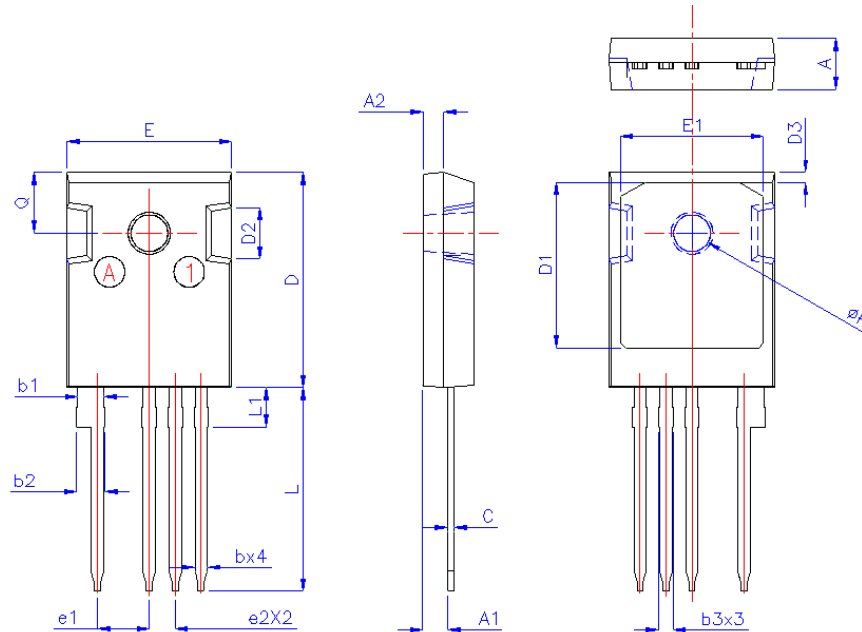


Fig18. Safe Operating Area



Package Drawing:

Dimensions (UNIT: mm)

SYMBDLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.9	5	5.1	0.193	0.197	0.201
A1	2.31	2.42	2.52	0.091	0.095	0.099
A2	1.9	2	2.1	0.075	0.079	0.083
b	1.16	1.22	1.27	0.046	0.048	0.050
b1	1.15	1.2	1.25	0.045	0.047	0.049
b2	2.61	2.76	2.91	0.103	0.109	0.115
b3	1.36	1.42	1.47	0.054	0.056	0.058
C	0.59	0.62	0.66	0.023	0.024	0.026
D	20.9	21	21.1	0.823	0.827	0.831
D1	15.94	16.24	16.54	0.628	0.639	0.651
D2		5		0.197 TYP		
D3	0.8	0.95	1.1	0.031	0.037	0.043
e	5.08 BSC				0.200 BSC	
e1	2.54 BSC				0.100BSC	
E	16.05	16.15	16.25	0.632	0.636	0.640
E1	13.82	14.02	14.26	0.544	0.552	0.561
L	19.75	19.95	20.15	0.778	0.785	0.793
L1	—	—	3.87	—	—	0.152
Q	5.95 BSC			0.234BSC		
ØP	3.45	3.6	3.75	0.136	0.142	0.148